

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L<sup>2</sup>-π-MOSV)

## 2SK2266

Chopper Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- 4 V gate drive
- Low drain-source ON resistance :  $R_{DS(ON)} = 22 \text{ m}\Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 27 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 60 \text{ V}$ )
- Enhancement-mode :  $V_{th} = 0.8\sim 2.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	60	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	60	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	45
	Pulse (Note 1)	$I_{DP}$	180
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	65	W
Single pulse avalanche energy (Note 2)	$E_{AS}$	246	mJ
Avalanche current	$I_{AR}$	45	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	6.5	mJ
Channel temperature	$T_{ch}$	150	°C
Storage temperature range	$T_{stg}$	-55~150	°C

### Thermal Characteristics

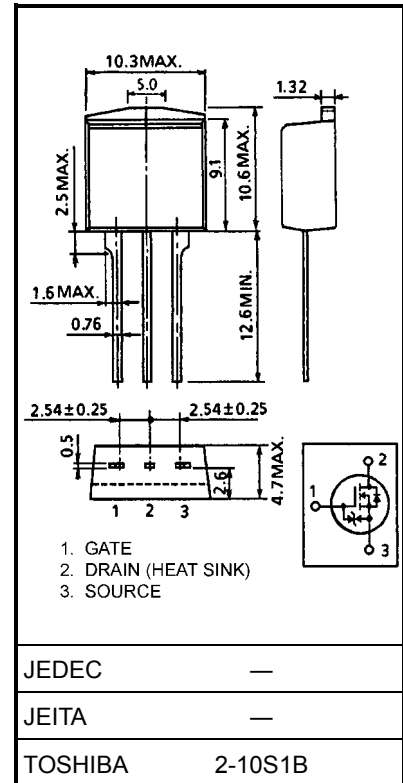
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.92	°C / W
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	83.3	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

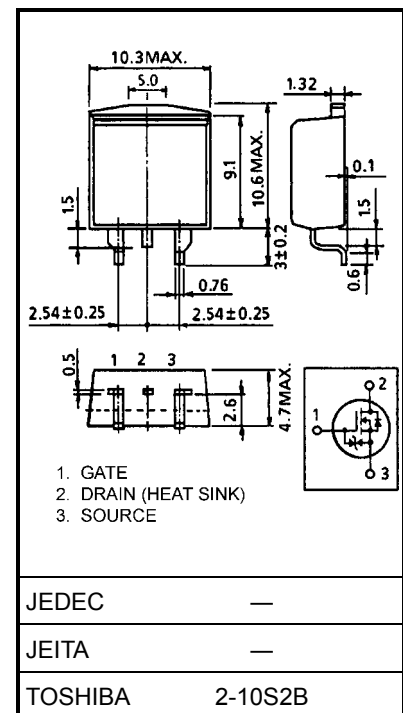
Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 165 \text{ }\mu\text{H}$ ,  $R_G = 25 \text{ }\Omega$ ,  $I_{AR} = 45 \text{ A}$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.  
Please handle with caution.



Weight: 1.5 g (typ.)



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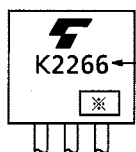
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	60	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.8	—	2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 15\text{ A}$	—	40	55	m $\Omega$
			$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$	—	22	30	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 25\text{ A}$	15	27	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1800	—	pF
Reverse transfer capacitance		$C_{rss}$		—	350	—	
Output capacitance		$C_{oss}$		—	900	—	
Switching time	Rise time	$t_r$	<p><math>I_D = 25\text{ A}</math> <math>V_{GS} = 10\text{ V}</math> <math>V_{DD} = 30\text{ V}</math> <math>R_L = 1.2\ \Omega</math> <math>t_w = 10\ \mu\text{s}</math> <math>\text{Duty} \leq 1\%</math></p>	—	20	—	ns
	Turn-on time	$t_{on}$		—	30	—	
	Fall time	$t_f$		—	40	—	
	Turn-off time	$t_{off}$		—	130	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 45\text{ A}$	—	60	—	nC
Gate-source charge		$Q_{gs}$		—	40	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	20	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	45	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	180	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.8	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 45\text{ A}, V_{GS} = 0\text{ V}, dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	90	—	ns
Reverse recovery charge	$Q_{rr}$		—	0.1	—	$\mu\text{C}$

## Marking

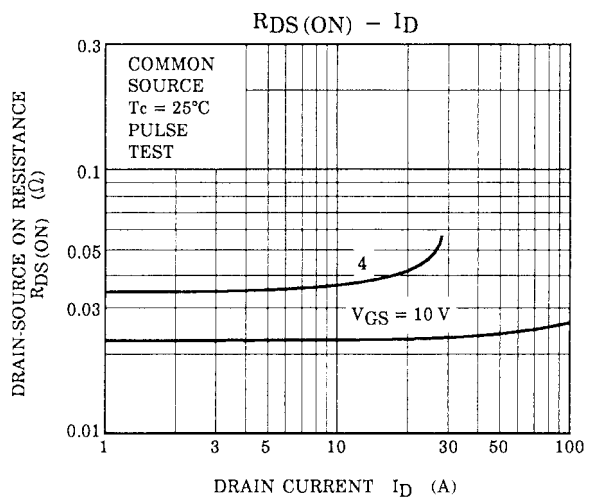
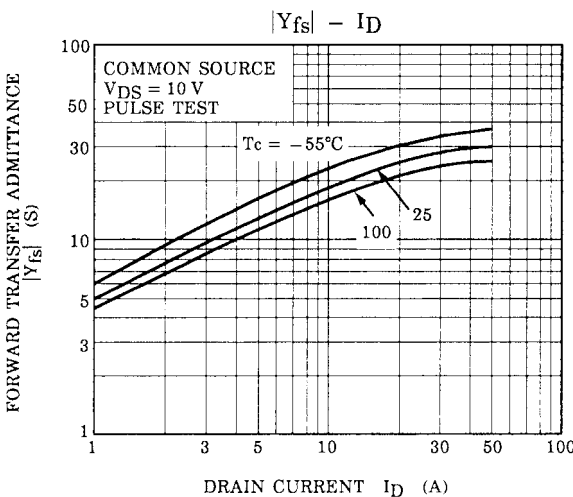
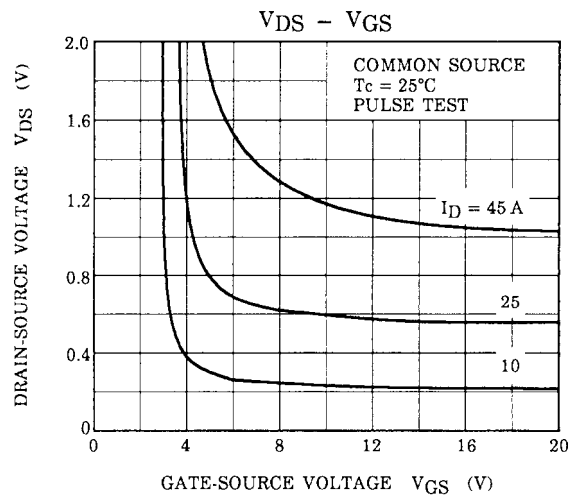
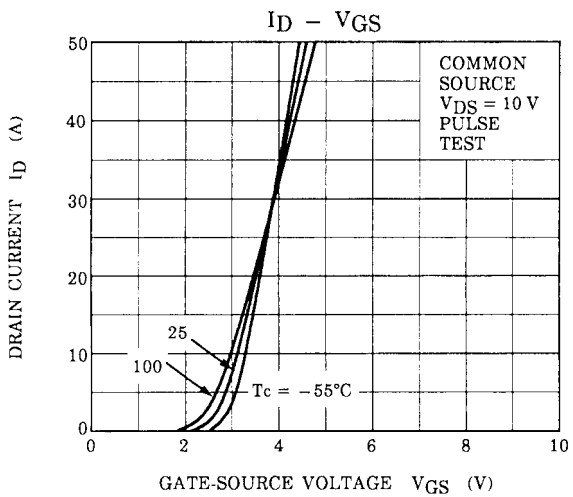
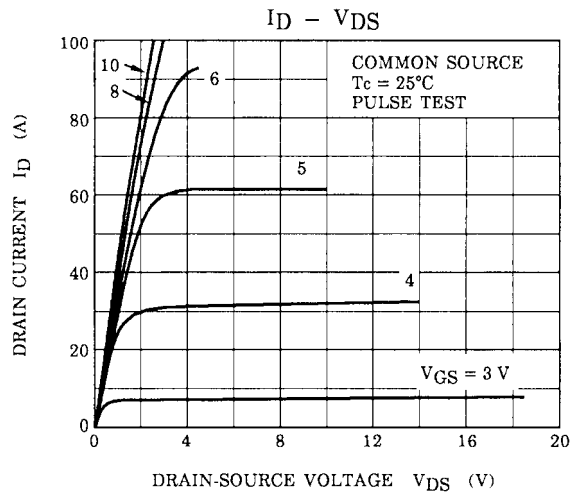
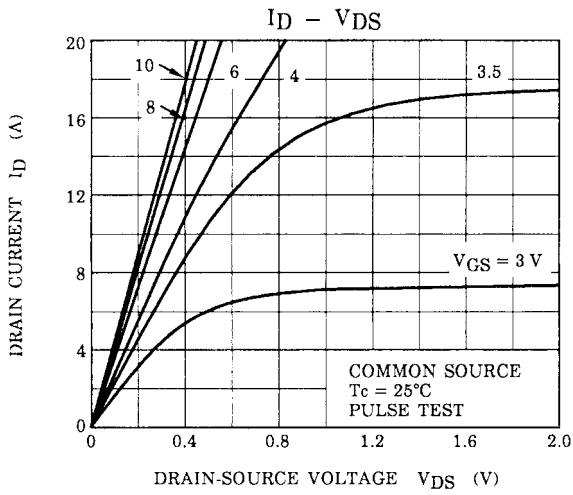


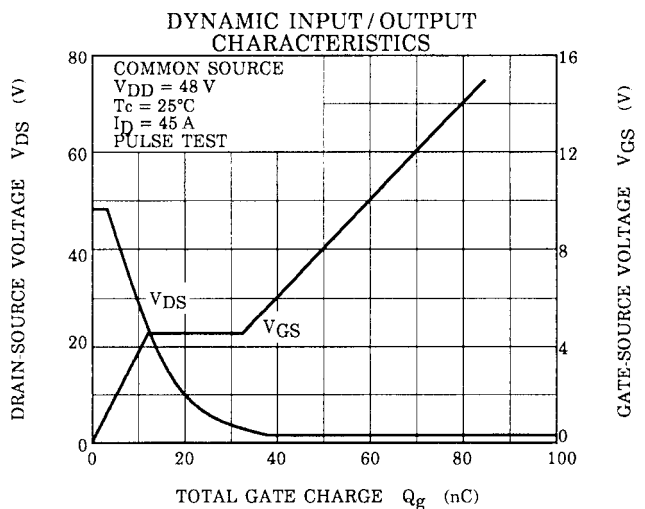
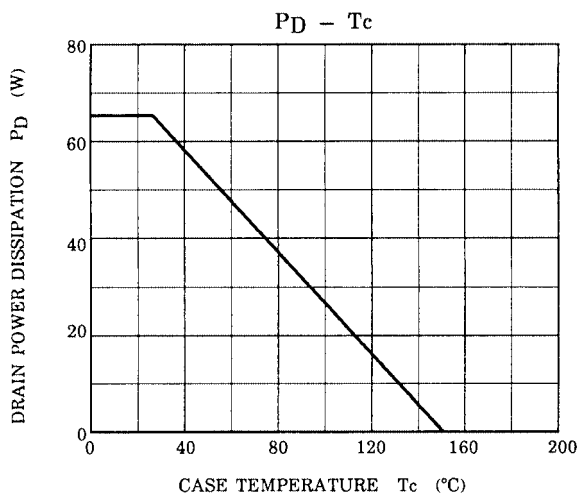
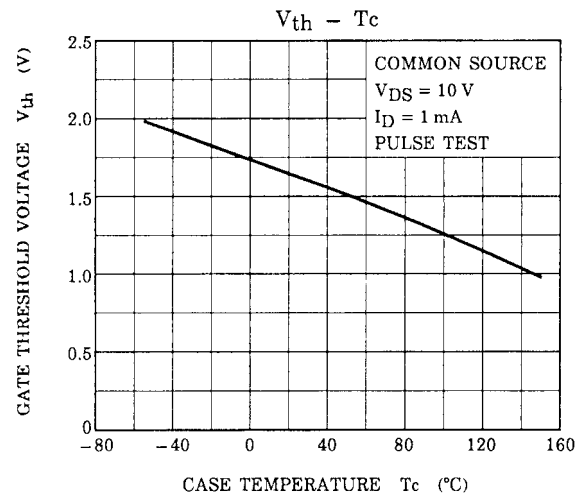
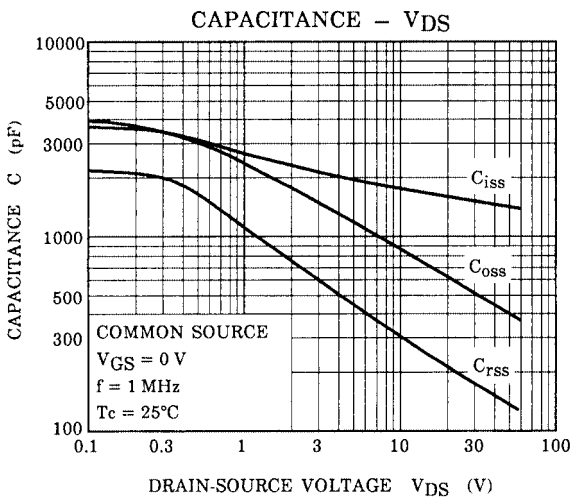
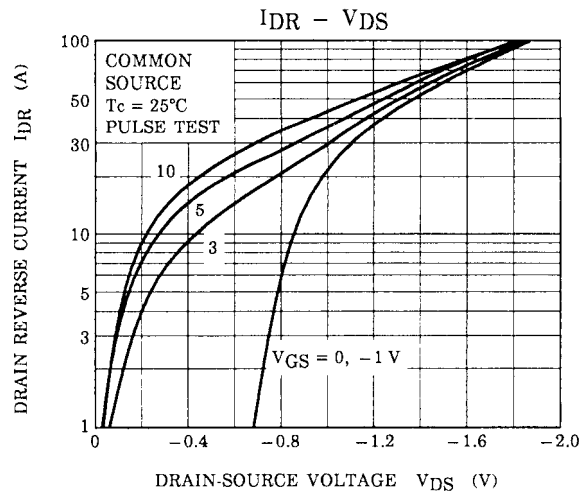
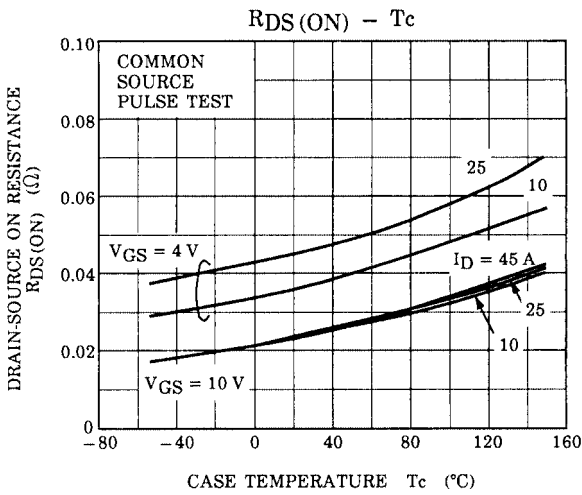
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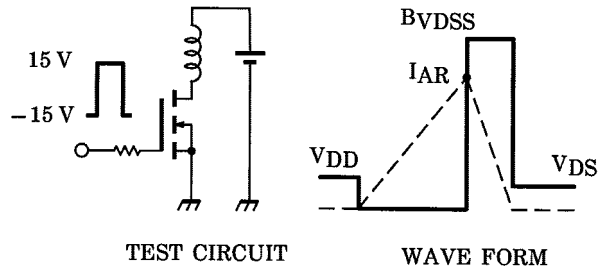
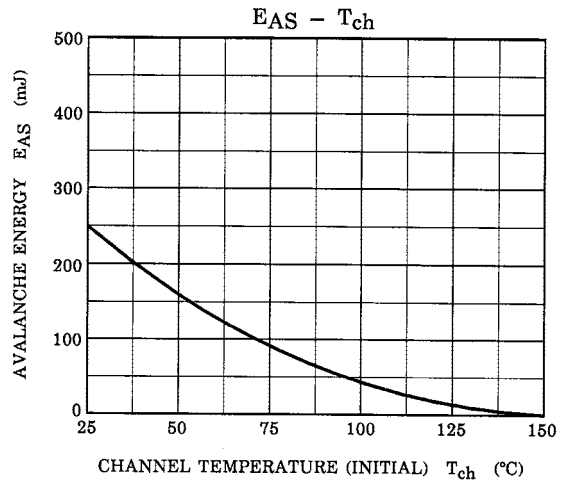
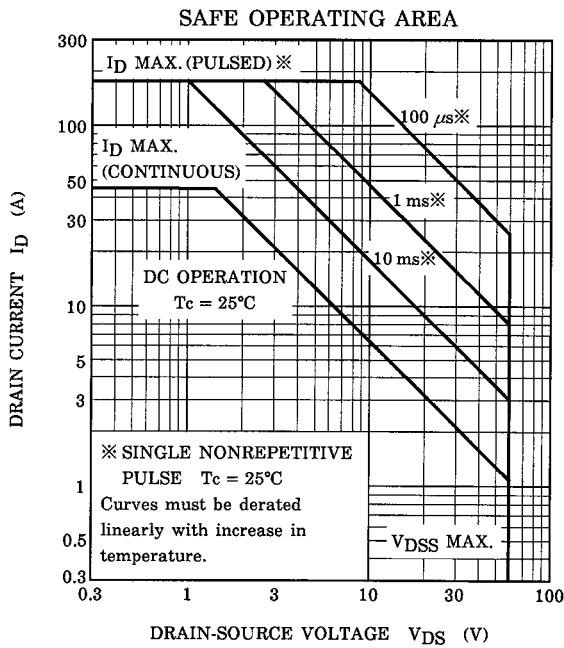
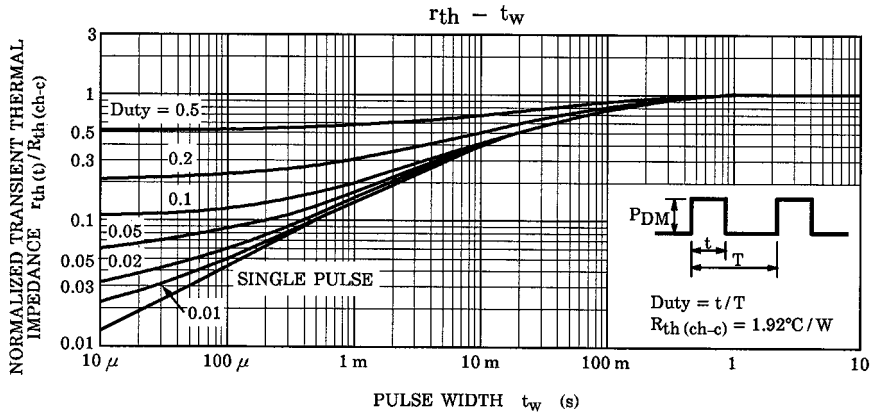
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







$R_G = 25 \Omega$   
 $V_{DD} = 25 V, L = 165 \mu H$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - VDD} \right)$$

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